

February 2014

### ISL9R30120G2

### 30 A 1200 V STEALTH™ Diode

### **Features**

- Stealth Recovery  $t_{rr}$  = 269 ns (@  $I_F$  = 30 A)
- Max Forward Voltage, V<sub>F</sub> = 3.3 V (@ T<sub>C</sub> = 25°C)
- 1200 V Reverse Voltage and High Reliability
- · Avalanche Energy Rated
- RoHS Compliant

### **Applications**

- Switch Mode Power Supplies
- · Hard Switched PFC Boost Diode
- UPS Free Wheeling Diode
- Motor Drive FWD
- SMPS FWD
- Snubber Diode

### **Description**

The ISL9R30120G2 is a STEALTH™ diode optimized for low loss performance in high frequency hard switched applications. The STEALTH™ family exhibits low reverse recovery current (I<sub>RR</sub>) and exceptionally soft recovery under typical operating conditions. This device is intended for use as a free wheeling or boost diode in power supplies and other power switching applications. The low I<sub>RR</sub> and short ta phase reduce loss in switching transistors. The soft recovery minimizes ringing, expanding the range of conditions under which the diode may be operated without the use of additional snubber circuitry. Consider using the STEALTH™ diode with an SMPS IGBT to provide the most efficient and highest power density design at lower cost.

## Package JEDEC STYLE 2 LEAD TO-247 ANODE CATHODE (BOTTOM SIDE METAL) A CATHODE

### **Device Maximum Ratings** $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Rating	Unit	
$V_{RRM}$	Repetitive Peak Reverse Voltage	1200	V	
V <sub>RWM</sub>	Working Peak Reverse Voltage	1200	V	
V <sub>R</sub>	DC Blocking Voltage	1200	V	
I <sub>F(AV)</sub>	Average Rectified Forward Current (T <sub>C</sub> = 80°C)	30	Α	
I <sub>FRM</sub>	Repetitive Peak Surge Current (20 kHz Square Wave)	70	Α	
I <sub>FSM</sub>	Nonrepetitive Peak Surge Current (Halfwave 1 Phase 60 Hz)	325	Α	
P <sub>D</sub>	Power Dissipation	166	W	
E <sub>AVL</sub>	Avalanche Energy (1 A, 40 mH)	20	mJ	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to 175	°C	
TL	Maximum Temperature for Soldering	300	°C	
$T_{PKG}$	Leads at 0.063 in (1.6 mm) from Case for 10 s Package Body for 10s, See Application Note AN-7528	260	°C	

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Part Number		Top Mark	Package	Packing Method	Tape V	Vidth	Quantity	
ISL9R30120G2 R30120G2		TO-247	Tube	N/A		30		
lectric	cal Chara	acteristics T <sub>C</sub> = 25	°C unless otherwi	se noted				
Symbol	Parameter		Test Conditions		Min	Тур	Max	Unit
ff State	Characte	ristics						
I <sub>R</sub>	Instantaneous Reverse Current		V <sub>R</sub> = 1200 V	T <sub>C</sub> = 25°C	-	-	100	μA
				T <sub>C</sub> = 125°C	-	-	1.0	mA
n State	Characte	ristics						
V <sub>F</sub>	Instantaneo	us Forward Voltage	I <sub>F</sub> = 30 A	T <sub>C</sub> = 25°C	_	2.8	3.3	V
•		· ·	i i	T <sub>C</sub> = 125°C	-	2.6	3.1	V
ynamic	Characte	ristics						
CJ	Junction Ca	pacitance	V <sub>R</sub> = 10 V, I <sub>F</sub> =	= 0 A	-	115	-	pF
witchin	g Charact	eristics				•		
t <sub>rr</sub> Reverse Recovery Time		covery Time	$I_F = 1 \text{ A, dI/dt} = 100 \text{ A/}\mu\text{s, V}_R = 15 \text{ V}$		-	45	56	ns
			$I_F = 30 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, V_R = 15 \text{ V}$		-	80	100	ns
t <sub>rr</sub>	Reverse Re	covery Time	I <sub>F</sub> = 30 A,		-	269	-	ns
Irr	Reverse Recovery Current		$dI_F/dt = 200 \text{ A/µs},$		-	7.5	-	Α
$Q_{rr}$	Reverse Re	covered Charge	$V_R = 780 \text{ V}, T_C = 25^{\circ}\text{C}$			930	-	nC
t <sub>rr</sub>	Reverse Re	covery Time	I <sub>F</sub> = 30 A,			529	-	ns
S	Softness Fa	ictor (t <sub>b</sub> /t <sub>a</sub> )	dI <sub>F</sub> /dt = 200 A/µs, V <sub>R</sub> = 780 V, T <sub>C</sub> = 125°C		-	6.2	-	-
I <sub>rr</sub>	Reverse Re	covery Current			-	11	-	Α
Q <sub>rr</sub>	Reverse Re	covered Charge	1C = 120 C			3.0	-	μC
t <sub>rr</sub>	Reverse Re	covery Time	I <sub>F</sub> = 30 A,		-	260	-	ns
S	Softness Fa	ictor (t <sub>b</sub> /t <sub>a</sub> )	dI <sub>F</sub> /dt = 1000 A/ $\mu$ s, V <sub>R</sub> = 780 V, T <sub>C</sub> = 125°C			4.8	-	-
I <sub>rr</sub>	Reverse Re	covery Current				30	-	Α
Q <sub>rr</sub>	Reverse Re	covered Charge				3.4	-	μC
dI <sub>M</sub> /dt	Maximum d	i/dt during t <sub>b</sub>				520	-	A/µ:
hermal	Characte	ristics				_		
$R_{\theta JC}$	Thermal Re	sistance Junction to Cas	e TO-247		-	-	0.75	°C/V
	Thermal Resistance Junction to Ambient TO-247						°C/V	

### Typical Performance Curves

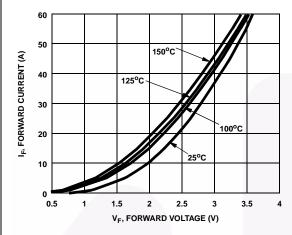


Figure 1. Forward Current vs Forward Voltage

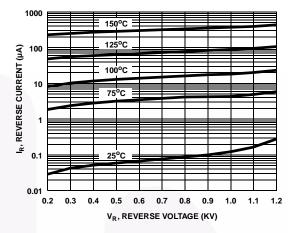


Figure 2. Reverse Current vs Reverse Voltage

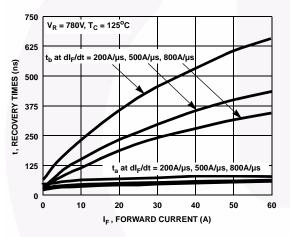


Figure 3. t<sub>a</sub> and t<sub>b</sub> Curves vs Forward Current

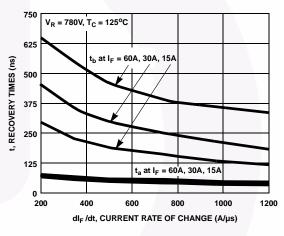


Figure 4. t<sub>a</sub> and t<sub>b</sub> Curves vs dl<sub>F</sub>/dt

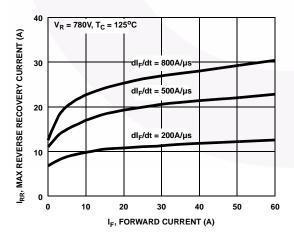


Figure 5. Maximum Reverse Recovery Current vs
Forward Current

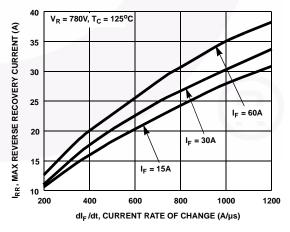
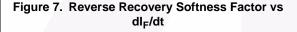


Figure 6. Maximum Reverse Recovery Current vs  $dI_F/dt$ 

# Typical Performance Curves (Continued) 9 V<sub>R</sub> = 780V, T<sub>C</sub> = 125°C V<sub>R</sub> = 780V, T<sub>C</sub> = 125°C



dI<sub>F</sub>/dt, CURRENT RATE OF CHANGE (A/μs)

800

600

200

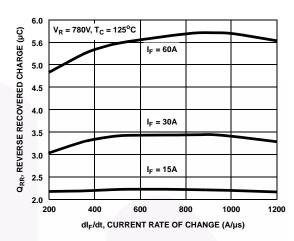


Figure 8. Reverse Recovery Charge vs  $\mathrm{dI}_{\mathrm{F}}/\mathrm{dt}$ 

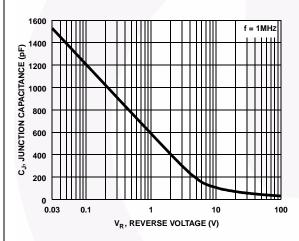


Figure 9. Junction Capacitance vs Reverse Voltage

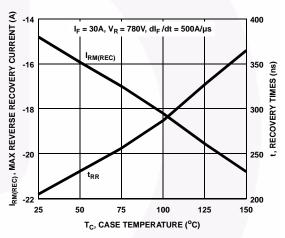
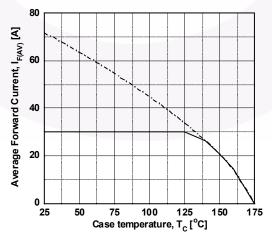


Figure 10. Maximum Reverse Recovery Current and t<sub>rr</sub> vs Case Temperature



1200

Figure 11. DC Current Derating Curve

### Typical Performance Curves (Continued)

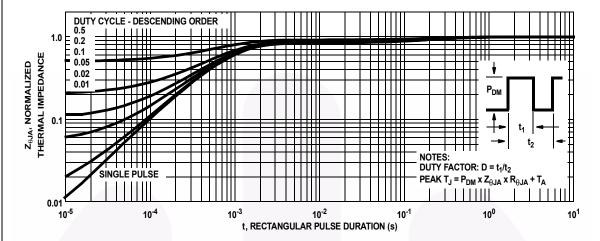
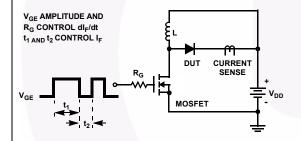


Figure 12. Normalized Maximum Transient Thermal Impedance

### Test Circuit and Waveforms



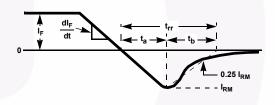
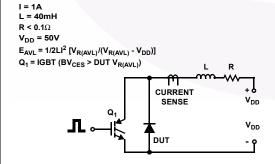


Figure 13. t<sub>rr</sub> Test Circuit

Figure 14. t<sub>rr</sub> Waveforms and Definitions



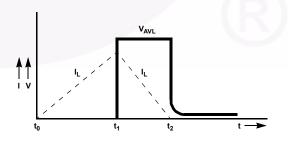
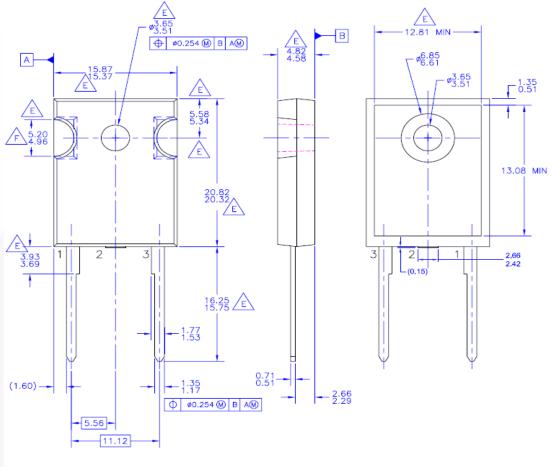


Figure 15. Avalanche Energy Test Circuit

Figure 16. Avalanche Current and Voltage Waveforms

### **Mechanical Dimensions**

### TO-247 2L



NOTES: UNLESS OTHERWISE SPECIFIED

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- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DRAWING CONFORMS TO ASME Y14.5 1994

E. DOES NOT COMPLY JEDEC STANDARD VALUE

F. NOTCH MAY BE SQUARE

G. DRAWING FILENAME; MKT-TO247B02\_REV02

### Figure 17. TO-247, Molded, 2LD, Jedec Option AB

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